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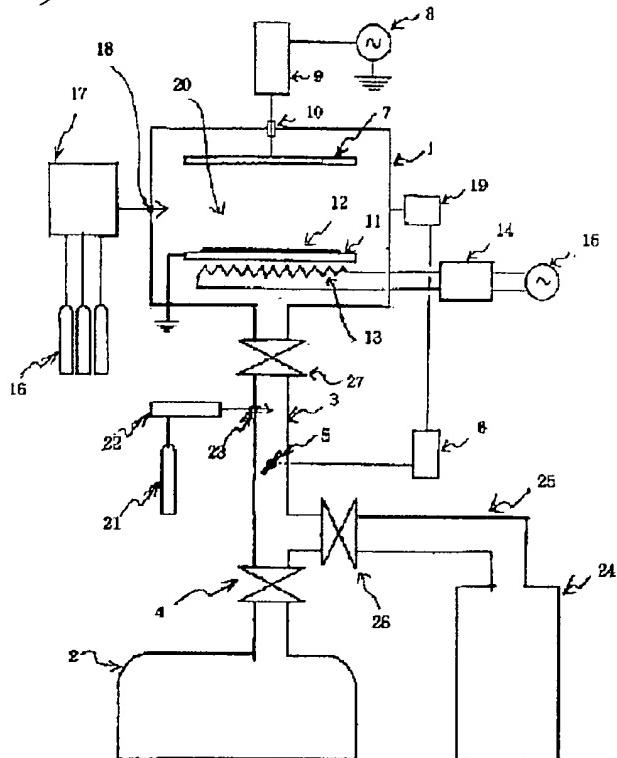
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INT.CL. : C23C 16/50 C23C 16/44 G03G 5/08
H01L 21/205 H01L 31/04TITLE : METHOD AND APPARATUS FOR
FORMING DEPOSITED FILM BY
PLASMA CVD METHOD

ABSTRACT : PROBLEM TO BE SOLVED: To provide a method and apparatus for forming deposited films by a plasma CVD method which eliminate or ameliorate the degradation in the discharge conductance and the operation defect of a conductance regulating valve by the adhesion of CVD byproduct in the plasma CVD method to a discharge piping and the conductance regulating valve and are capable of manufacturing amorphous and microcrystal semiconductors having a high grade when applied to the deposited film forming apparatus and method which dislike dry etching.

SOLUTION: This deposited film forming method or apparatus by the plasma CVD method forms the functional deposited films while regulating the pressure of a deposited film forming chamber by the conductance regulating valve installed on the discharge piping from the deposited film forming chamber to a discharge pump. In such a case, an inert gas is introduced into the discharge piping 3 from the deposited film forming chamber 1 to the discharge pump 2 after the end of the deposited film formation or in the process of the deposited film formation to suck and remove the powder which is the CVD byproduct adhered to the discharge piping 3 and the conductance regulating valve 5 formed at the time of the deposited film formation into a dust collector 24 disposed on the piping branched from the discharge piping 3.

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